# NX3L2267

# Low-ohmic dual single-pole double-throw analog switch

Rev. 5 — 18 June 2012

**Product data sheet** 

### 1. General description

The NX3L2267 is a dual low-ohmic single-pole double-throw analog switch suitable for use as an analog or digital 2:1 multiplexer/demultiplexer. Each switch has a digital select input (nS), two independent inputs/outputs (nY0 and nY1) and a common input/output (nZ).

Schmitt trigger action at the digital inputs makes the circuit tolerant to slower input rise and fall times. Low threshold digital inputs allows this device to be driven by 1.8 V logic levels in 3.3 V applications without significant increase in supply current  $I_{CC}$ . This makes it possible for the NX3L2267 to switch 4.3 V signals with a 1.8 V digital controller, eliminating the need for logic level translation. The NX3L2267 allows signals with amplitude up to  $V_{CC}$  to be transmitted from nZ to nY0 or nY1, or from nY0 or nY1 to nZ. Its low ON resistance (0.5  $\Omega$ ) and flatness (0.13  $\Omega$ ) ensures minimal attenuation and distortion of transmitted signals.

#### 2. Features and benefits

- Wide supply voltage range from 1.4 V to 4.3 V
- Very low ON resistance (peak):
  - 1.65  $\Omega$  (typical) at  $V_{CC} = 1.4 \text{ V}$
  - 0.95  $\Omega$  (typical) at  $V_{CC} = 1.65 \text{ V}$
  - 0.55 Ω (typical) at V<sub>CC</sub> = 2.3 V
  - 0.50 Ω (typical) at V<sub>CC</sub> = 2.7 V
  - 0.50  $\Omega$  (typical) at  $V_{CC} = 4.3 \text{ V}$
- Break-before-make switching
- High noise immunity
- ESD protection:
  - ♦ HBM JESD22-A114F Class 3A exceeds 7500 V
  - ♦ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
  - ◆ IEC61000-4-2 contact discharge exceeds 6000 V for switch ports
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD 78B Class II Level A
- 1.8 V control logic at V<sub>CC</sub> = 3.6 V
- Control input accepts voltages above supply voltage
- Very low supply current, even when input is below V<sub>CC</sub>
- High current handling capability (350 mA continuous current under 3.3 V supply)
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C



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## 3. Applications

- Cell phone
- PDA
- Portable media player

## 4. Ordering information

#### Table 1. Ordering information

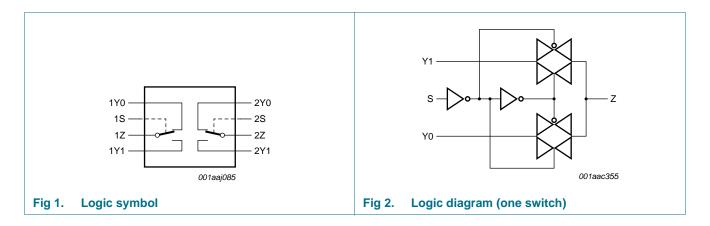
Type number	Package			
	Temperature range	Name	Description	Version
NX3L2267GM	–40 °C to +125 °C	XQFN10	plastic extremely thin quad flatpackage; no leads; 10 terminals; body $2 \times 1.55 \times 0.5$ mm	SOT1049-3
NX3L2267GU	–40 °C to +125 °C	XQFN10	plastic, extremely thin quad flat package; no leads; 10 terminals; body $1.40 \times 1.80 \times 0.50$ mm	SOT1160-1

## 5. Marking

#### Table 2. Marking

Type number	Marking code
NX3L2267GM	M67
NX3L2267GU	M7

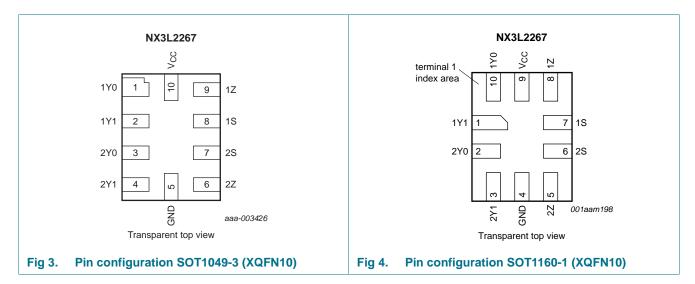
## 6. Functional diagram



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## 7. Pinning information

#### 7.1 Pinning



#### 7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT1049-3	SOT1160-1	
1Y0	1	10	independent input or output
1Y1	2	1	independent input or output
2Y0	3	2	independent input or output
2Y1	4	3	independent input or output
GND	5	4	ground (0 V)
2Z	6	5	common output or input
2S	7	6	select input
1S	8	7	select input
1Z	9	8	common output or input
V <sub>CC</sub>	10	9	supply voltage

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### 8. Functional description

Table 4. Function table[1]

Input nS	Channel on
L	nY0 = nZ
Н	nY1 = nZ

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

### 9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
VI	input voltage	select input nS	<u>[1]</u> –0.5	+4.6	V
V <sub>SW</sub>	switch voltage		<u>[2]</u> –0.5	$V_{CC} + 0.5$	V
I <sub>IK</sub>	input clamping current	$V_1 < -0.5 \text{ V}$	-50	-	mΑ
I <sub>SK</sub>	switch clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±50	mΑ
I <sub>SW</sub>	switch current	$V_{SW} > -0.5 \text{ V or } V_{SW} < V_{CC} + 0.5 \text{ V};$ source or sink current	-	±350	mA
		$V_{SW}$ > -0.5 V or $V_{SW}$ < $V_{CC}$ + 0.5 V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	±500	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[3][4]	250	mW

<sup>[1]</sup> The minimum input voltage rating may be exceeded if the input current rating is observed.

## 10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		1.4	4.3	V
VI	input voltage	select input nS	0	4.3	V
V <sub>SW</sub>	switch voltage	switch input nY0 or nY1	<u>[1]</u> 0	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 1.4 V to 4.3 V	[2]	200	ns/V

<sup>[1]</sup> To avoid sinking GND current from terminal nZ when switch current flows in terminal nYn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no GND current will flow from terminal nYn. In this case, there is no limit for the voltage drop across the switch.

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<sup>[2]</sup> The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed but may not exceed 4.6 V.

<sup>[3]</sup> For XQFN10 (SOT1049-3) package: above 132 °C the value of Ptot derates linearly with 14.1 mW/K.

<sup>[4]</sup> For XQFN10 (SOT1160-1) package: above 128 °C the value of Ptot derates linearly with 11.5 mW/K.

<sup>[2]</sup> Applies to select input nS signal levels.

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## 11. Static characteristics

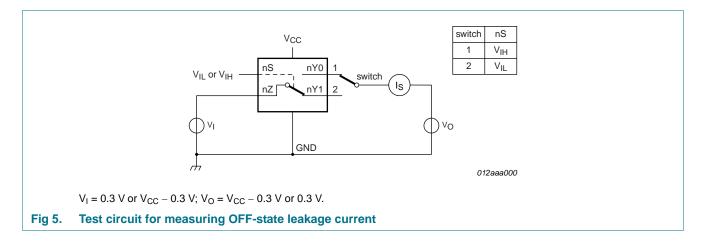
Table 7. Static characteristics

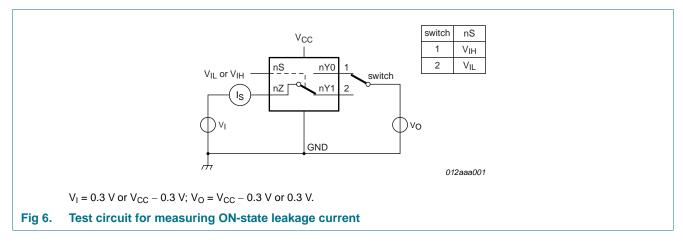
At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	Ta	<sub>mb</sub> = 25	°C	T <sub>amb</sub> =	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max (85 °C)	Max (125 °C)	
** *	HIGH-level	V <sub>CC</sub> = 1.4 V to 1.6 V	0.9	-	-	0.9	-	-	V
	input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.9	-	-	0.9	-	-	٧
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.1	-	-	1.1	-	-	٧
		V <sub>CC</sub> = 2.7 V to 3.6 V	1.3	-	-	1.3	-	-	٧
		V <sub>CC</sub> = 3.6 V to 4.3 V	1.4	-	-	1.4	-	-	V
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 1.4 V to 1.6 V	-	-	0.3	-	0.3	0.3	V
	input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	0.4	-	0.4	0.3	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.5	-	0.5	0.4	٧
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.5	-	0.5	0.5	٧
		V <sub>CC</sub> = 3.6 V to 4.3 V	-	-	0.6	-	0.6	0.6	٧
l <sub>l</sub>	input leakage current	select input nS; V <sub>I</sub> = GND to 4.3 V; V <sub>CC</sub> = 1.4 V to 4.3 V	-	-	-	-	±0.5	±1	μΑ
I <sub>S(OFF)</sub>	OFF-state	nYn port; see Figure 5							
	leakage	V <sub>CC</sub> = 1.4 V to 3.6 V	-	-	±5	-	±10	±100	nΑ
	current	$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	-	±10	-	±50	±200	nΑ
S(ON)	ON-state	nZ port; see Figure 6							
	leakage	$V_{CC} = 1.4 \text{ V to } 3.6 \text{ V}$	-	-	±5	-	±20	±200	nΑ
	current	$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	-	±10	-	±50	±400	nΑ
lcc	supply current	$V_I = V_{CC}$ or GND; $V_{SW} = GND$ or $V_{CC}$							
		V <sub>CC</sub> = 3.6 V	-	-	100	-	300	3000	nΑ
		V <sub>CC</sub> = 4.3 V	-	-	150	-	500	5000	nΑ
Δl <sub>CC</sub>	additional	$V_{SW} = GND \text{ or } V_{CC}$							
	supply current	V <sub>I</sub> = 2.6 V; V <sub>CC</sub> = 4.3 V	-	2.0	4.0	-	7	7	μΑ
		$V_{I} = 2.6 \text{ V}; V_{CC} = 3.6 \text{ V}$	-	0.35	0.7	-	1	1	μΑ
		V <sub>I</sub> = 1.8 V; V <sub>CC</sub> = 4.3 V	-	7.0	10.0	-	15	15	μΑ
		V <sub>I</sub> = 1.8 V; V <sub>CC</sub> = 3.6 V	-	2.5	4.0	-	5	5	μΑ
		V <sub>I</sub> = 1.8 V; V <sub>CC</sub> = 2.5 V	-	50	200	-	300	500	nΑ
Cı	input capacitance		-	1.0	-	-	-	-	pF
C <sub>S(OFF)</sub>	OFF-state capacitance	port nYn	-	35	-	-	-	-	pF
C <sub>S(ON)</sub>	ON-state capacitance	port nYn	-	135	-	-	-	-	pF

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#### 11.1 Test circuits





#### Low-ohmic dual single-pole double-throw analog switch

#### 11.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see Figure 8 to Figure 14.

Symbol	Parameter	Conditions		-40 °C to +85 °C			-40 °C to +125 °C	
			Min	Typ[1]	Max	Min	Max	
R <sub>ON(peak)</sub>	ON resistance (peak)	port nYn; $V_I = GND$ to $V_{CC}$ ; $I_{SW} = 100$ mA; see Figure 7						
		$V_{CC} = 1.4 \text{ V}$	-	1.65	3.7	-	4.1	Ω
		$V_{CC} = 1.65 \text{ V}$	-	0.95	1.6	-	1.7	Ω
		V <sub>CC</sub> = 2.3 V	-	0.55	0.8	-	0.9	Ω
		$V_{CC} = 2.7 \text{ V}$	-	0.50	0.75	-	0.9	Ω
		V <sub>CC</sub> = 4.3 V	-	0.50	0.75	-	0.9	Ω
$\Delta R_{ON}$	ON resistance mismatch between channels	$V_I = GND \text{ to } V_{CC};$ $I_{SW} = 100 \text{ mA}$						
		V <sub>CC</sub> = 1.4 V	-	0.20	0.35	-	0.35	Ω
		V <sub>CC</sub> = 1.65 V	-	0.20	0.25	-	0.30	Ω
		V <sub>CC</sub> = 2.3 V	-	0.09	0.13	-	0.15	Ω
		$V_{CC} = 2.7 \text{ V}$	-	0.09	0.125	-	0.15	Ω
		V <sub>CC</sub> = 4.3 V	-	0.09	0.125	-	0.15	Ω
R <sub>ON(flat)</sub>	ON resistance (flatness)	port nYn; $V_I = GND$ to $V_{CC}$ ; $I_{SW} = 100 \text{ mA}$						
		V <sub>CC</sub> = 1.4 V	-	1.05	3.35	-	3.65	Ω
		V <sub>CC</sub> = 1.65 V	-	0.55	1.25	-	1.35	Ω
		V <sub>CC</sub> = 2.3 V	-	0.20	0.35	-	0.40	Ω
		V <sub>CC</sub> = 2.7 V	-	0.18	0.35	-	0.40	Ω
		V <sub>CC</sub> = 4.3 V	-	0.23	0.40	-	0.45	Ω

<sup>[1]</sup> Typical values are measured at  $T_{amb}$  = 25 °C.

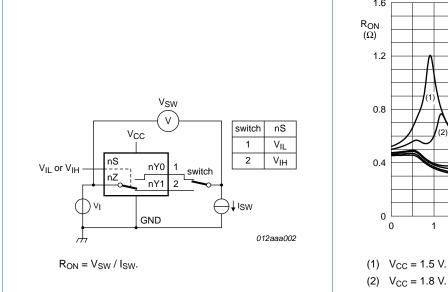
<sup>[2]</sup> Measured at identical  $V_{CC}$ , temperature and input voltage.

<sup>[3]</sup> Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V<sub>CC</sub> and temperature.

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### 11.3 ON resistance test circuit and graphs



001aag564 1.6 2 V<sub>I</sub> (V)

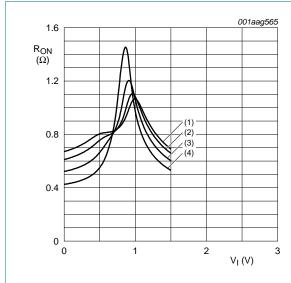
- (3)  $V_{CC} = 2.5 \text{ V}.$
- (4)  $V_{CC} = 2.7 \text{ V}.$
- (5)  $V_{CC} = 3.3 \text{ V}.$
- (6)  $V_{CC} = 4.3 \text{ V}.$

Measured at  $T_{amb} = 25$  °C.

Test circuit for measuring ON resistance

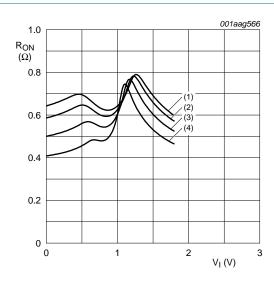
Typical ON resistance as a function of input Fig 8. voltage (Yn port)

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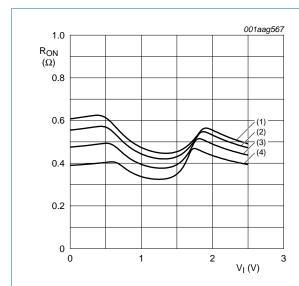
- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig 9. ON resistance as a function of input voltage;  $V_{CC} = 1.5 \text{ V (nYn port)}$ 



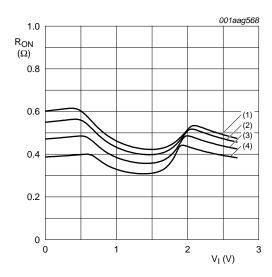
- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig 10. ON resistance as a function of input voltage;  $V_{CC} = 1.8 \text{ V (nYn port)}$ 



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

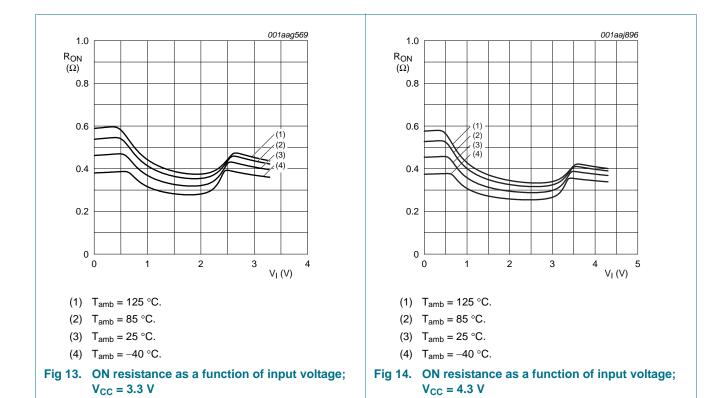
Fig 11. ON resistance as a function of input voltage;  $V_{CC} = 2.5 \text{ V (nYn port)}$ 



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \,^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .
- (4)  $T_{amb} = -40 \, ^{\circ}C$ .

Fig 12. ON resistance as a function of input voltage;  $V_{CC} = 2.7 \text{ V (nYn port)}$ 

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### 12. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see Figure 17.

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t <sub>en</sub>	enable time	nS to nZ or nYn; see <u>Figure 15</u>							
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	50	90	-	120	120	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	36	70	-	80	90	ns
		$V_{CC}$ = 2.3 V to 2.7 V	-	24	45	-	50	55	ns
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	22	40	-	45	50	ns
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	22	40	-	45	50	ns
t <sub>dis</sub>	disable time	nS to nZ or nYn; see <u>Figure 15</u>							
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	32	70	-	80	90	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	20	55	-	60	65	ns
		$V_{CC}$ = 2.3 V to 2.7 V	-	12	25	-	30	35	ns
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	10	20	-	25	30	ns
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	10	20	-	25	30	ns

#### Low-ohmic dual single-pole double-throw analog switch

 Table 9.
 Dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see Figure 17.

Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t <sub>b-m</sub> brea time	break-before-make	see Figure 16 [2]							
	time	$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	19	-	9	-	-	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	17	-	7	-	-	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	13	-	4	-	-	ns
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	10	-	3	-	-	ns
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	10	-	2	-	-	ns

<sup>[1]</sup> Typical values are measured at  $T_{amb}$  = 25 °C and  $V_{CC}$  = 1.5 V, 1.8 V, 2.5 V, 3.3 V and 4.3 V respectively.

#### 12.1 Waveform and test circuits

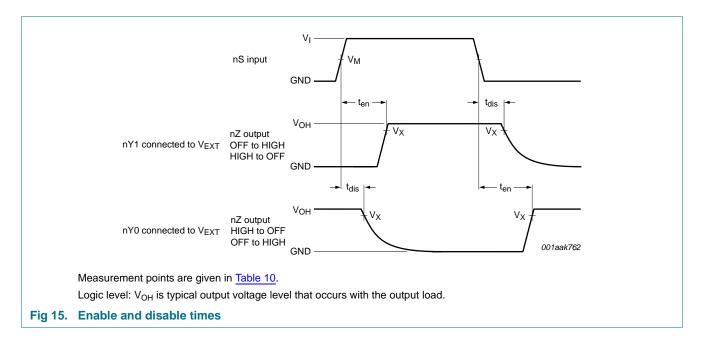
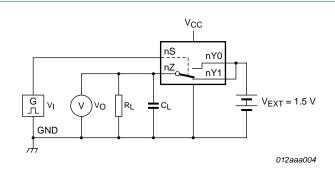


Table 10. Measurement points

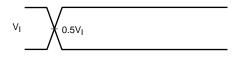
Supply voltage	Input	Output
V <sub>CC</sub>	V <sub>M</sub>	V <sub>X</sub>
1.4 V to 4.3 V	0.5V <sub>CC</sub>	0.9V <sub>OH</sub>

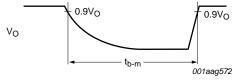
<sup>[2]</sup> Break-before-make guaranteed by design.

#### Low-ohmic dual single-pole double-throw analog switch



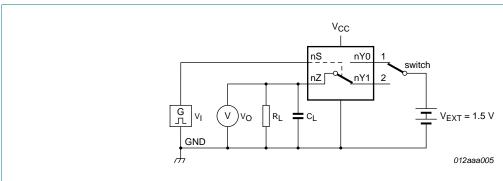
a. Test circuit.





b. Input and output measurement points

Fig 16. Test circuit for measuring break-before-make timing



Test data is given in Table 11.

Definitions test circuit:

R<sub>L</sub> = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $V_{EXT}$  = External voltage for measuring switching times.

Fig 17. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load	
V <sub>CC</sub>	VI	t <sub>r</sub> , t <sub>f</sub>	CL	R <sub>L</sub>
1.4 V to 4.3 V	$V_{CC}$	≤ 2.5 ns	35 pF	50 Ω

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#### Low-ohmic dual single-pole double-throw analog switch

## 12.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

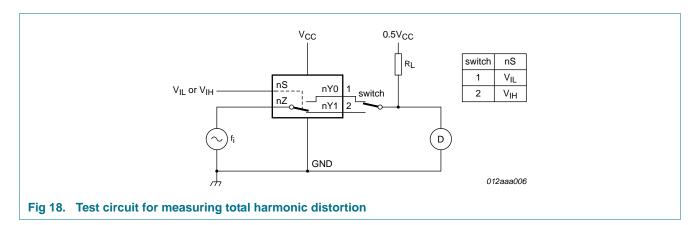
At recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $V_l = \text{GND}$  or  $V_{\text{CC}}$  (unless otherwise specified);  $t_r = t_f \le 2.5$  ns.

Symbol	Parameter	Conditions		T <sub>amb</sub> = 25 °C			Unit
				Min	Тур	Max	
THD	total harmonic distortion	$f_i$ = 20 Hz to 20 kHz; $R_L$ = 32 $\Omega$ ; see Figure 18	<u>[1]</u>		'		
		$V_{CC} = 1.4 \text{ V}; V_I = 1 \text{ V (p-p)}$		-	0.15	-	%
		$V_{CC} = 1.65 \text{ V}; V_I = 1.2 \text{ V (p-p)}$		-	0.10	-	%
		$V_{CC} = 2.3 \text{ V}; V_{I} = 1.5 \text{ V (p-p)}$		-	0.02	-	%
		$V_{CC} = 2.7 \text{ V}; V_1 = 2 \text{ V (p-p)}$		-	0.02	-	%
		$V_{CC} = 4.3 \text{ V}; V_1 = 2 \text{ V (p-p)}$		-	0.02	-	%
		$V_{CC}$ = 3.0 V; $V_{I}$ = 1 V (p-p); $R_{L}$ = 600 $\Omega$		-	0.01	-	%
f <sub>(-3dB)</sub>	–3 dB frequency response	$R_L = 50 \Omega$ ; see Figure 19	<u>[1]</u>				
		port nYn; $V_{CC}$ = 1.4 V to 4.3 V		-	60	-	MHz
$lpha_{iso}$	isolation (OFF-state)	$f_i$ = 100 kHz; $R_L$ = 50 $\Omega$ ; see Figure 20	<u>[1]</u>				
		V <sub>CC</sub> = 1.4 V to 4.3 V		-	-90	-	dB
V <sub>ct</sub>	crosstalk voltage	between digital inputs and switch; $f_i = 1 \text{ MHz}$ ; $C_L = 50 \text{ pF}$ ; $R_L = 50 \Omega$ ; see Figure 21					
		V <sub>CC</sub> = 1.4 V to 3.6 V		-	0.21	-	V
		V <sub>CC</sub> = 3.6 V to 4.3 V		-	0.30	-	V
Xtalk	crosstalk	between switches; $f_i = 100 \text{ kHz}$ ; $R_L = 50 \Omega$ ; see Figure 22	[1]				
		V <sub>CC</sub> = 1.4 V to 4.3 V		-	-90	-	dB
Q <sub>inj</sub>	charge injection	$f_i$ = 1 MHz; $C_L$ = 0.1 nF; $R_L$ = 1 M $\Omega$ ; $V_{gen}$ = 0 V; $R_{gen}$ = 0 $\Omega$ ; see Figure 23					
		V <sub>CC</sub> = 1.5 V		-	4	-	рС
		V <sub>CC</sub> = 1.8 V		-	6	-	рС
		V <sub>CC</sub> = 2.5 V		-	16	-	рС
		V <sub>CC</sub> = 3.3 V		-	24	-	рС
		V <sub>CC</sub> = 4.3 V		-	37	-	рС

<sup>[1]</sup>  $f_i$  is biased at  $0.5V_{CC}$ .

#### Low-ohmic dual single-pole double-throw analog switch

#### 12.3 Test circuits



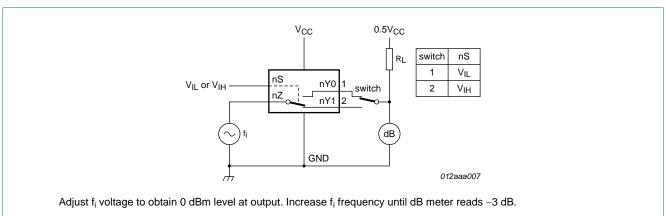
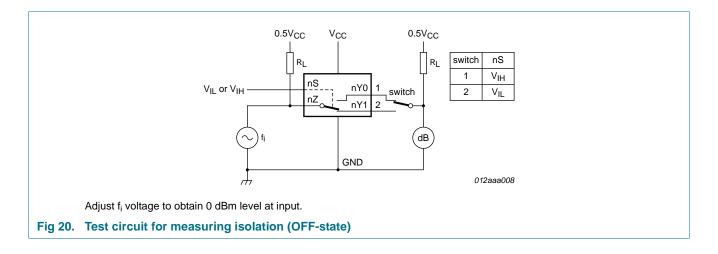
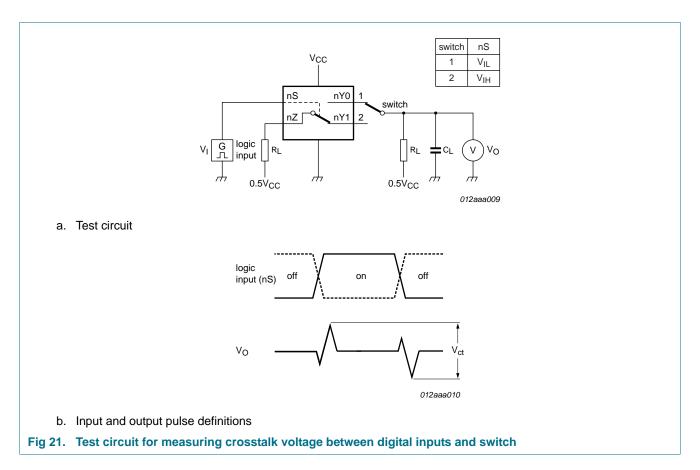
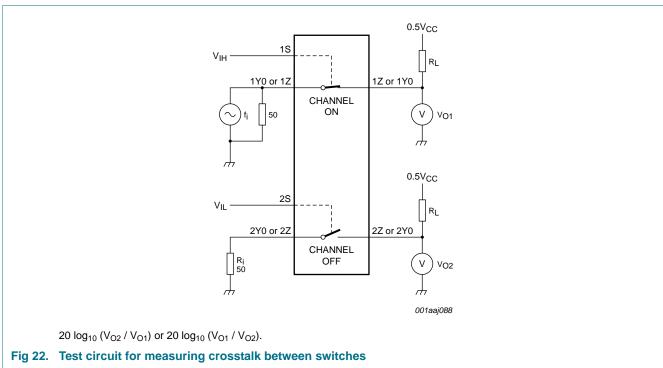


Fig 19. Test circuit for measuring the frequency response when channel is in ON-state

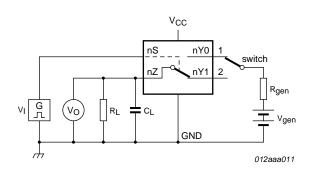


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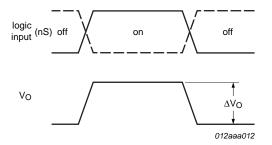




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a. Test circuit.



b. Input and output pulse definitions

Definition:  $Q_{inj} = \Delta V_O \times C_L$ .

 $\Delta V_{O}$  = output voltage variation.

R<sub>gen</sub> = generator resistance.

 $V_{gen}$  = generator voltage.

Fig 23. Test circuit for measuring charge injection

#### Low-ohmic dual single-pole double-throw analog switch

## 13. Package outline

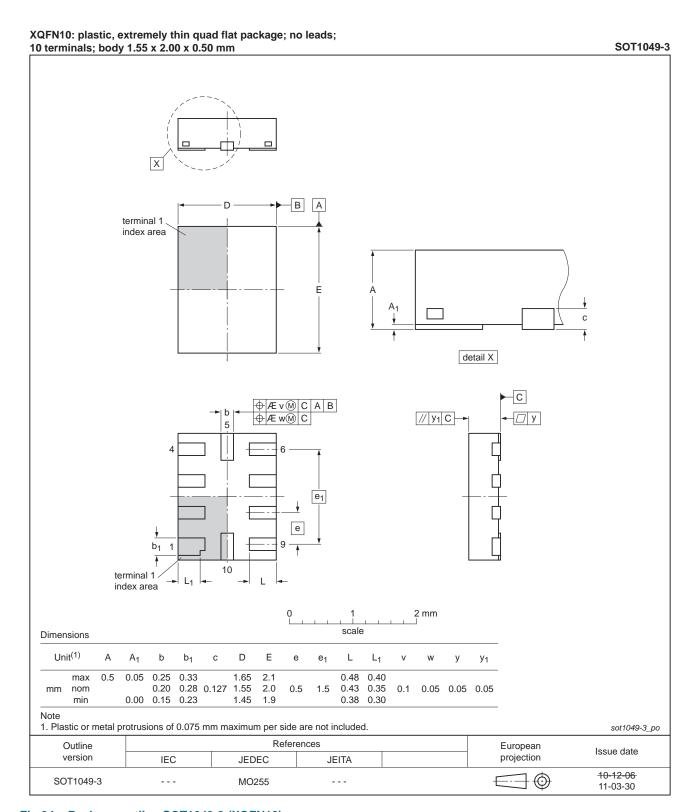


Fig 24. Package outline SOT1049-3 (XQFN10)

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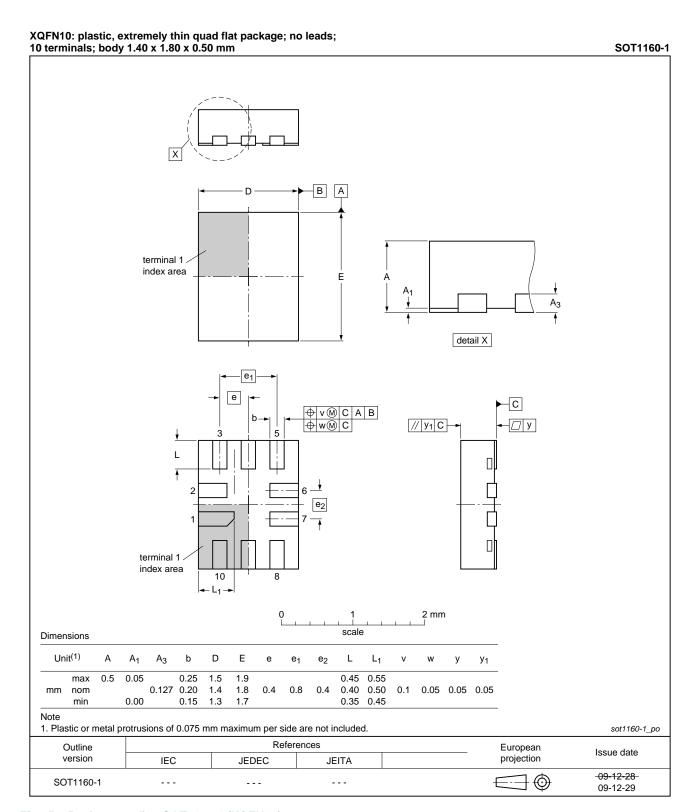


Fig 25. Package outline SOT1160-1 (XQFN10)

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#### Low-ohmic dual single-pole double-throw analog switch

## 14. Abbreviations

#### Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

## 15. Revision history

#### Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3L2267 v.5	20120618	Product data sheet	-	NX3L2267 v.4
Modifications:	<ul> <li>Package outl</li> </ul>	ine drawing SOT1049-2 chanç	ged to SOT1049-3 ( <u>Fig</u>	jure 24).
NX3L2267 v.4	20111108	Product data sheet	-	NX3L2267 v.3
Modifications:	<ul> <li>Legal pages</li> </ul>	updated.		
NX3L2267 v.3	20101223	Product data sheet	-	NX3L2267 v.2
NX3L2267 v.2	20100713	Product data sheet	-	NX3L2267 v.1
NX3L2267 v.1	20091109	Product data sheet	-	-

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### 16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### Low-ohmic dual single-pole double-throw analog switch

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